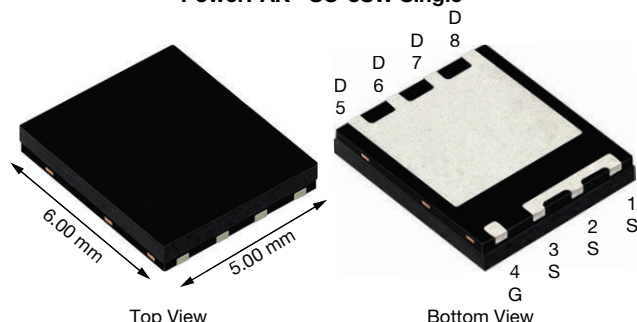


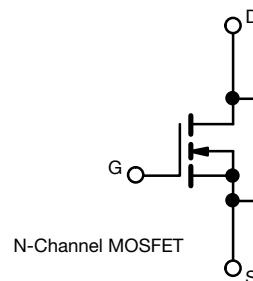
Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PowerPAK® SO-8SW Single


FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE


PRODUCT SUMMARY

V_{DS} (V)	40
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.00072
I_D (A) ^e	467
Configuration	Single

ORDERING INFORMATION

Package	PowerPAK® SO-8SW
Lead (Pb)-free and halogen-free	SQRS140EP (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	40	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current ^e	I_D	$T_C = 25$ °C	A
		$T_C = 125$ °C	
Continuous source current (diode conduction)	I_S	246	
Pulsed drain current ^{a, e}	I_{DM}	1353	
Single pulse avalanche current	I_{AS}	71.5	mJ
Single pulse avalanche energy			
	E_{AS}	255	
Maximum power dissipation ^a	P_D	$T_C = 25$ °C	W
		$T_C = 125$ °C	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^c		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R_{thJA}	42	°C/W
Junction-to-case (drain) ^d	R_{thJC}	0.56	

Notes

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- As per on JESD51-14
- Values based on R_{thJC} and T_C of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system

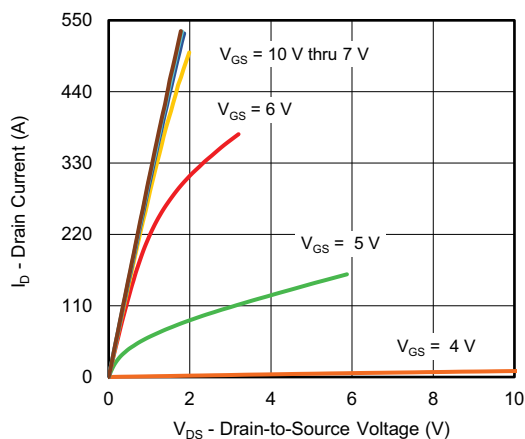
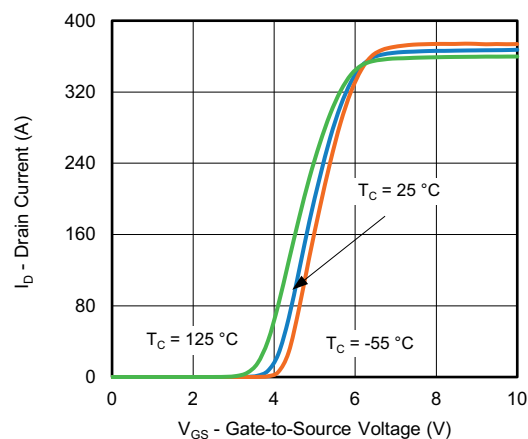
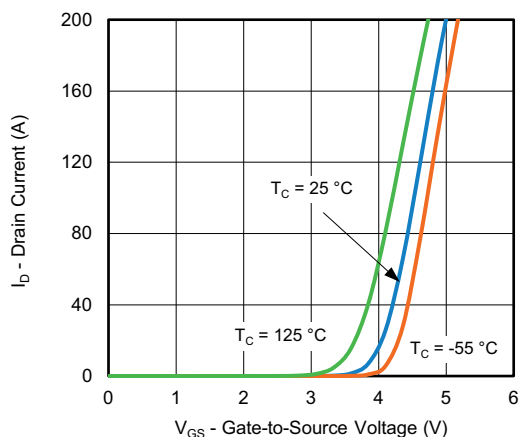
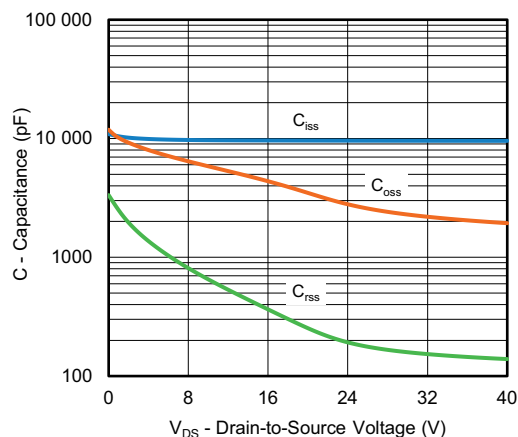
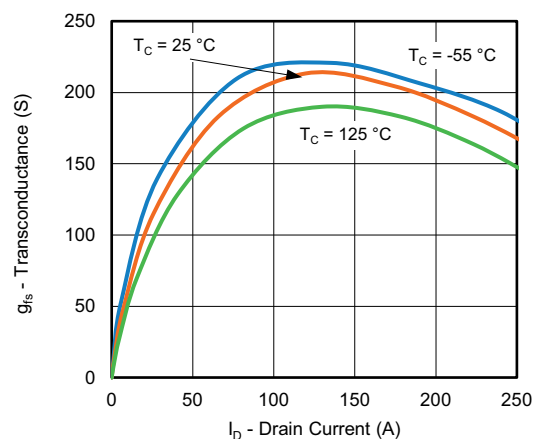
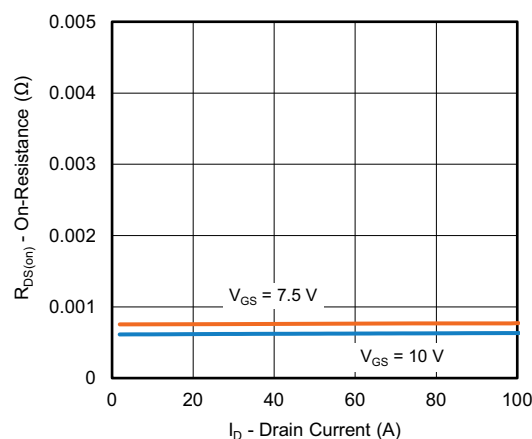


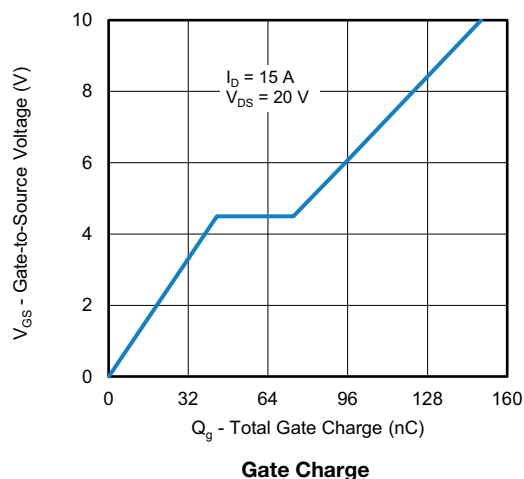
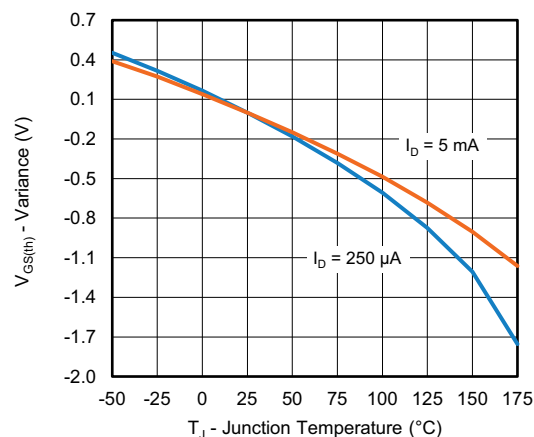
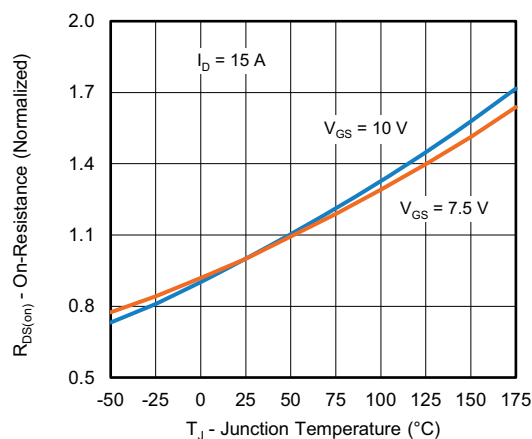
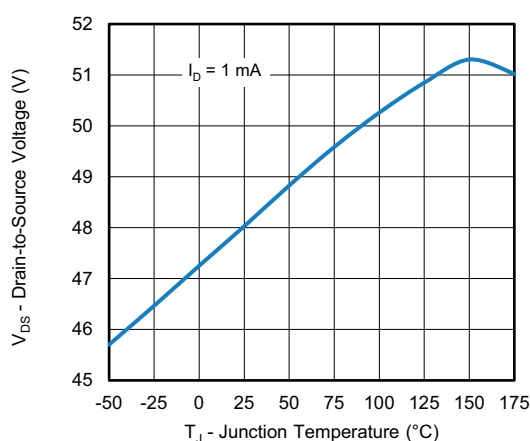
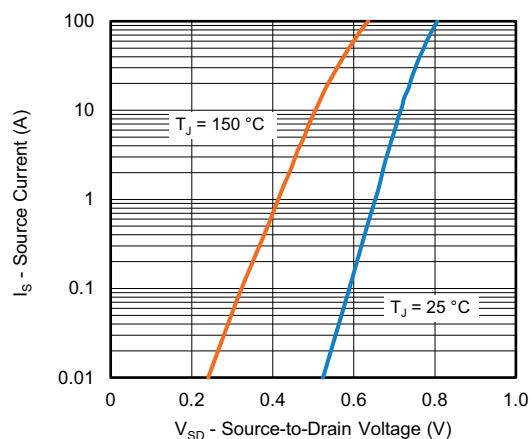
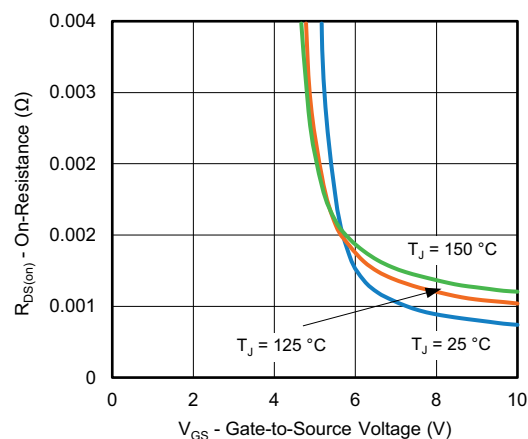
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2	2.8	3.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	250	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	30	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A	-	0.00058	0.00072	Ω
		V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.0010	
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.0012	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 25 A		-	115	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	9554	13 376	pF
Output capacitance	C _{oss}			-	2720	3808	
Reverse transfer capacitance	C _{rss}			-	184	258	
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 15 A	-	148	222	nC
Gate-source charge ^c	Q _{gs}			-	44	-	
Gate-drain charge ^c	Q _{gd}			-	30	-	
Gate resistance	R _g	f = 1 MHz		0.6	1.3	2	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 20 V, R _L = 1.33 Ω I _D ≅ 15 A, V _{GEN} = 10 V, R _g = 1 Ω		-	26	39	ns
Rise time ^c	t _r			-	35	53	
Turn-off delay time ^c	t _{d(off)}			-	52	78	
Fall time ^c	t _f			-	17	26	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	986	A
Forward voltage	V _{SD}	I _F = 15 A, V _{GS} = 0 V		-	-	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 15 A, di/dt = 100 A/μs		-	78	156	ns
Body diode reverse recovery charge	Q _{rr}			-	163	326	nC
Reverse recovery fall time	t _a			-	49	-	ns
Reverse recovery rise time	t _b			-	30	-	
Body diode peak reverse recovery current	I _{RM(REC)}					-	3.6

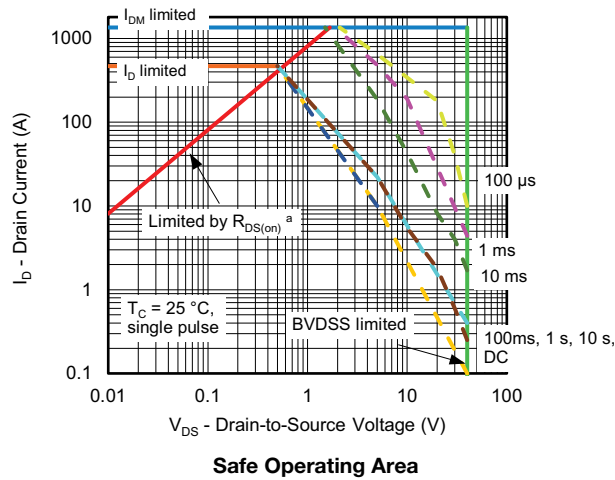
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transfer Characteristics

Capacitance

Transconductance

On-Resistance vs. Drain Current

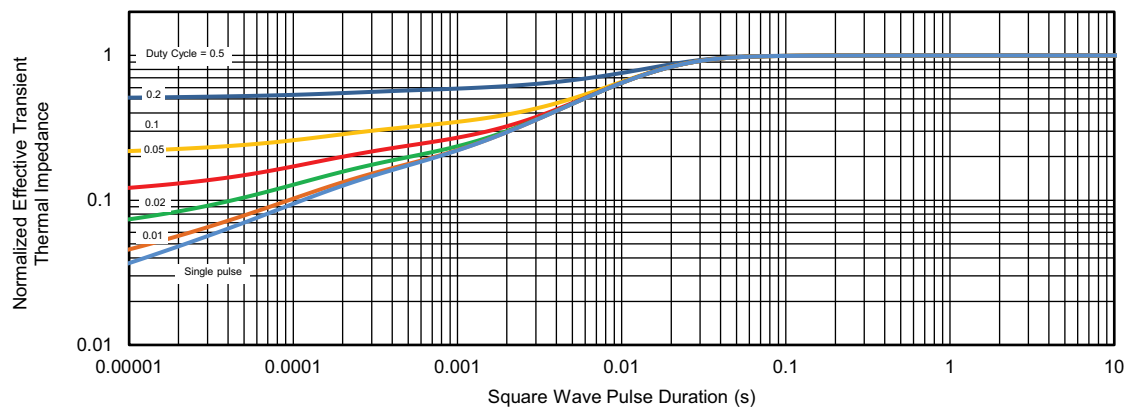
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Gate Charge

Threshold Voltage

On-Resistance vs. Junction Temperature

Drain Source Breakdown vs. Junction Temperature

Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to Source Voltage


Note

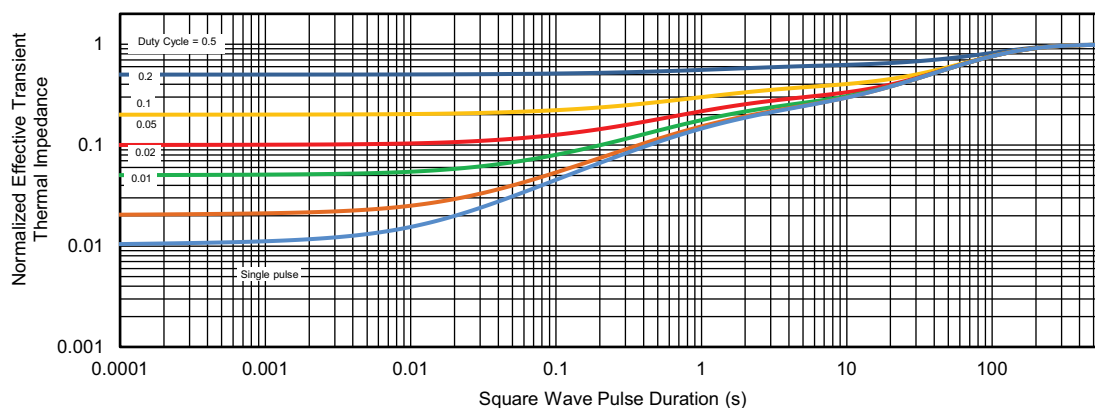
a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case



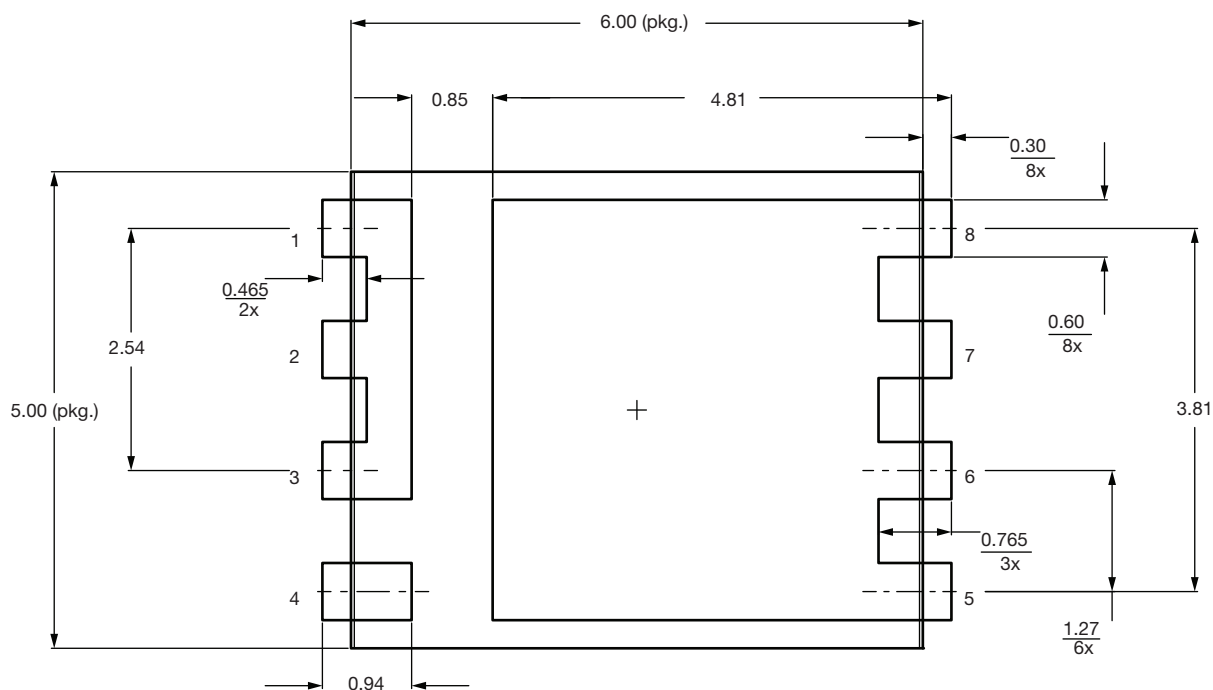
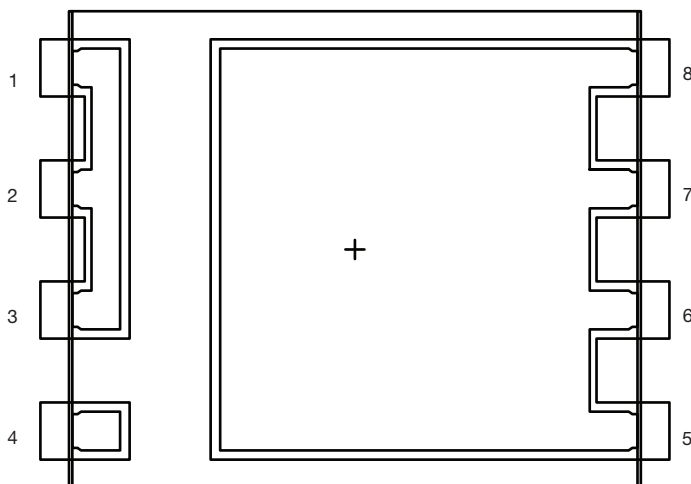
Normalized Thermal Transient Impedance, Junction-to-Ambient

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?621546.

Recommended Land Pattern PowerPAK® SO-8SW (PKSO8SWSCL)


Note

- Dimensions in mm

ECN: C24-0483-Rev. A, 20-May-2024
DWG: 3027



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